NSN 5961-01-476-2269

Diode Semiconductor Device - Page 1 of 1



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Voltage Rating In Volts Per Characteristic:

18.0 reverse breakdown voltage, instantaneous and 22.0 reverse breakdown voltage, instantaneous

Current Rating Per Characteristic:

1.00 milliamperes drain current pascal

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius ambient air

Special Features:

Diode is a 5 amp, 580 watt, bipolar transient suppressor, dual die; each die is glass passivated; metalization material is nickel and gold plated (ni-ni-au); standoff voltage (vso) 16.20 volts; max. Reverse leakage (ir) at vso is 1 microamp; max. Clamping voltage (vcl) 29.1 volts at peak pulse current (ipp) 17.5 amps

Precious Material And Location:

Plating gold

Precious Material:

Gold

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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